

LM(2)5190(-Q1) CCCV Buck Converter Design Tool



About

 = Input Box

TERMS OF USE

Step 1: Operating Specifications

Input Voltage – Min, $V_{SUPPLY(MIN)}$	23.0 V
Input Voltage – Typ, $V_{SUPPLY(TYP)}$	24.0 V
Input Voltage – Max, $V_{SUPPLY(MAX)}$	24.0 V
Regulation Target in CV, V_{LOAD}	23.5 V
Regulation Target in CC / Full load current in CV, I_{LOAD}	10.0 A
Switching Frequency, f_{SW}	470.0 kHz
Switching Mode	FPWM
Device P/N	LM5190(-Q1)
Frequency Set Resistor, R_{RT}	49.9 kΩ

Step 2: Current Sense Resistor

Required Peak Inductor C/L Setpoint at $V_{SUPPLY(MAX)}$, I_{PEAKCL}	12.0 Apk
Recommended Maximum Sense Resistance	4.5 mΩ
Selected Sense Resistance, R_S	4.0 mΩ
Power Loss at C/L, P_{RS}	0.58 W

Step 3: Buck Inductor

Recommended Inductance for 40% Pk-Pk Ripple Current at $V_{SUPPLY(TYP)}$	0.26 μH
Minimum Inductance	-0.16 μH
Selected Buck Inductance, L_{OUT}	3.30 μH
Peak Inductor Current at $V_{SUPPLY(MAX)}$ and Full Load (CV mode)	10.2 Apk
Peak Inductor Current Limit (I_{LIMIT}) at $V_{SUPPLY(MAX)}$	16.5 Apk
Switching Skip at $V_{SUPPLY(MAX)}$	doesn't happen
Dropout Mode Operation at $V_{SUPPLY(TYP)}$	can happen

Step 4: C_{VCC} , C_{BOOT} , C_{VIN} , R_{PGOOD} , T_{SSCV}

VCC Capacitor, C_{VCC}	2.2 μF
Boot Capacitor, C_{BOOT}	100 nF
VIN pin Capacitor, C_{VIN}	220 nF
Power Good Pull-up Resistor, R_{PGOOD}	100 kΩ
Internal Soft-start Time in CV mode, T_{SSCV}	2.75 ms

Step 5: Enable, UVLO

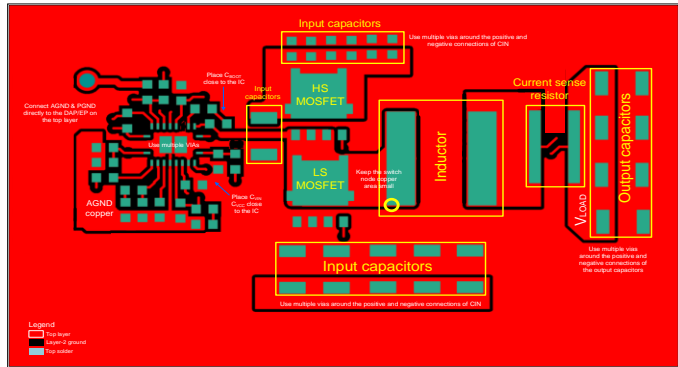
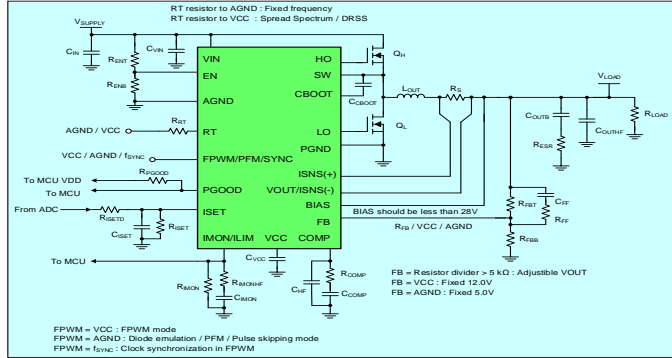
Desired Start-up Voltage	4.0 V
Upper Enable Resistor for UVLO, R_{ENT}	100.0 kΩ
Lower Enable Resistor for UVLO, R_{ENL}	35.59 kΩ
Estimated Shutdown Voltage	3.6 V

Step 6: Output Capacitors

Desired Undershoot during 50% Load Transient in FPWM (CV mode)	6.0 %
Desired Crossover Frequency, $f_{CROSS(desired)}$ (CV mode)	28.0 kHz
Minimum Derated Output Capacitance	20.2 μF
Rated Output Capacitance (Bulk/SuperCap), C_{OUTB}	424 μF
Derating Factor (Bulk/SuperCap)	0.5
Derated Output Capacitance (Bulk/SuperCap)	212.0 μF
Effective Capacitor ESR (Bulk/SuperCap), R_{ESRB}	5 mΩ
Rated Output Capacitance (Ceramic Capacitor/Local C_{OUT}), C_{OUTHF}	0.1 μF
Derating Factor (Ceramic Capacitor)	0.7
Derated Output Capacitance (Ceramic Capacitor)	0.1 μF
Effective Capacitor ESR (Ceramic Capacitor), R_{ESRHF}	1 mΩ
Derated Output Capacitance (Total)	212.1 μF
Estimated Output Voltage Ripple at $V_{SUPPLY(TYP)}$ (CV mode)	0.1 mVpk-pk
Estimated Overshoot (when switching stops at full-load to no-load) (CV mode)	0.1 %
Estimated Undershoot (during no-load to full-load transition in FPWM) (CV mode)	7.5 %

Step 7: Feedback Resistors (CV mode)

Upper Feedback Resistance, R_{FBT}	150.0 kΩ
Lower Standard Feedback Resistance, R_{FBB}	5.29 kΩ



Step 8: Loop Compensation Design (CV mode)

Load Pole Frequency, f_{LP}	0.4 kHz
ESR Zero Frequency, f_{ESRZ}	149 kHz
Desired Maximum R_{COMP}	43.84 k Ω
Desired Minimum C_{COMP}	1.3 nF
Desired C_{HF}	24 pF
Desired Compensation Zero Frequency	2.25 kHz
Desired Compensation Pole Frequency	153 kHz
Selected R_{COMP}	5.90 kΩ
Selected C_{COMP}	12.00 nF
Selected C_{HF}	47 pF
Selected Compensation Zero Frequency, f_{COMPZ}	2.25 kHz
Selected Compensation Pole Frequency, f_{COMPF}	576 kHz
Selected Feedforward Capacitance, C_{FF}	1 pF
Selected Feedforward Resistance, R_{FF}	1000 kΩ
Selected C_{FF} Zero Frequency, f_{CFFZ}	1061 kHz

Step 9: ISET Components (CC mode)

Desired ISET Voltage, V_{ISET}	1.80 V
ISET Resistor, R_{ISET}	OPEN or 120 k Ω
Selected ISET Capacitor, C_{ISET}	100 nF
Current Regulation Soft-start Time, T_{SSCC}	10.0 ms

Step 10: Loop Compensation Design (CC mode)

Desired R_{IMON}	17.14 k Ω
Desired Minimum C_{IMON}	29.07 nF
Desired R_{IMONHF}	36.46 Ω
Desired IMON Pole Frequency	0.3 kHz
Desired IMON Zero Frequency	150 kHz
Selected R_{IMON}	26.10 kΩ
Selected C_{IMON}	10.00 nF
Selected R_{IMONHF}	0.000 Ω
Selected IMON Pole Frequency, f_{IMONP}	0.6 kHz
Selected IMON Zero Frequency, f_{IMONZ}	>2000 kHz

Step 11: Efficiency

Inductor	
Inductor DCR at 25°C, R_{DCR}	3.9 m Ω
Estimated Inductor Core Loss at $V_{SUPPLY(typ)}$	1.6 W
MOSFETS High-side Low-side	
On-State Resistance at 25°C, $R_{DS(on)}$	0.5 0.5 m Ω
Total Gate Charge, Q_G	11 11 nC
Gate-Drain Charge, Q_{GD}	3 3 nC
Gate-Source Charge, Q_{GS}	5 5 nC
Output Charge, Q_{OSS}	7 7 nC
Output Capacitance, C_{OSS}	150 150 pF
Gate Resistance, R_G	1.0 1.0 Ω
Transconductance, g_{FS}	52 52 S
Gate-Source Threshold Voltage, V_{TH}	3.1 3.1 V
Body Diode Forward Voltage, V_{SD}	0.8 0.8 V
Body Diode Rev Recovery Charge, Q_{RR}	41 41 nC
Thermal Resistance, θ_{JA}	62 62 °C/W
External Schottky Diode (if applicable)	
Schottky Fwd Voltage, V_{FWDsch}	0.0 V
Schottky Rev Recovery Charge, Q_{RRsch}	0 nC

Step 12: IC Power Loss

External BIAS from V_{LOAD}	Yes
Ambient Temperature (T_A)	100 °C
Estimated IC Power Dissipation, P_{IC}	0.25 W
Estimated Junction Temperature (eT _J)	111.0 °C
MOSFET driving current	10.34 mA

Step 13: Input Capacitors

Input Voltage Ripple Spec	50 mVpk-pk
Minimum Derated Input Capacitance, C_{IN}	106.4 μ F
Maximum Input Capacitor RMS Current	5.0 A(rms)
Maximum Input Capacitor ESR	5 m Ω

